

Trench MOS Barrier Schottky Rectifier

Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

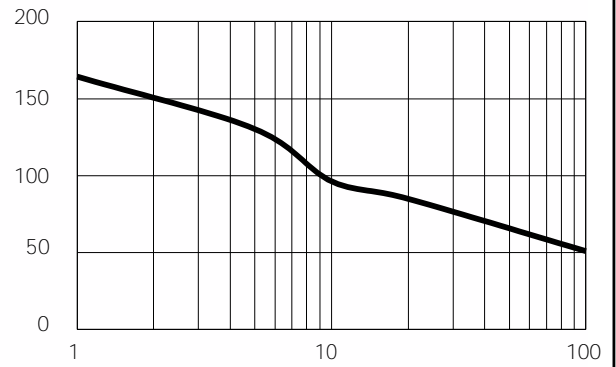
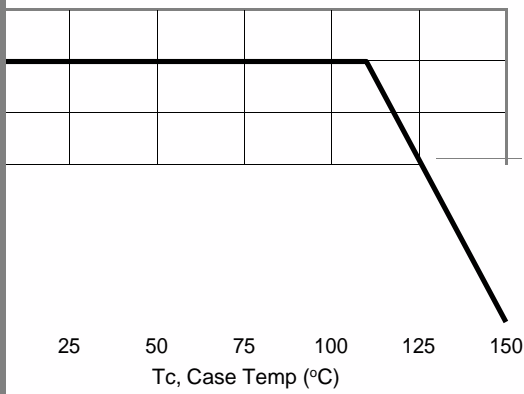
Parameter		Symbol	Limit		Unit
Maximum repetitive peak reverse voltage		VRRM	100		V
Maximum average forward rectified current		IF(AV)	10		A
Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode		IFSM	160		A
Operating junction and storage temperature range		TJ, TSTG	-50 to +150		
Typical thermal resistance per leg		R _{JC}	22		°C/W
Instantaneous forward voltage per diode			TYP.	MAX.	V
	IF= A	TJ=125°C	0.4		
	IF=10A	TJ=125°C	0.		
Instantaneous reverse current per diode at rated reverse voltage		TJ=25°C	0		uA
		TJ=125°C	40		mA

Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width 0.40 ms

INGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



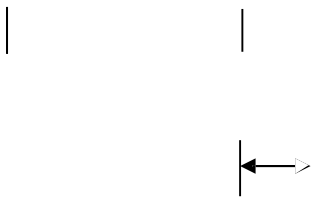
Tj=150

ROHM

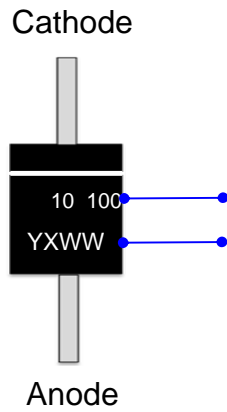
M



PACKAGE OUTLINE DIMENSIONS

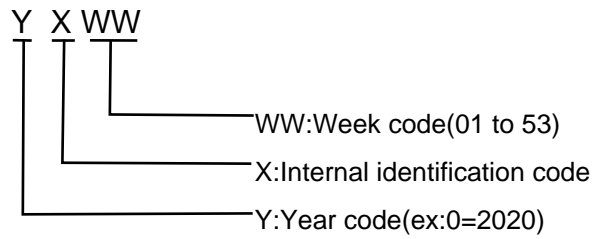


Marking Information



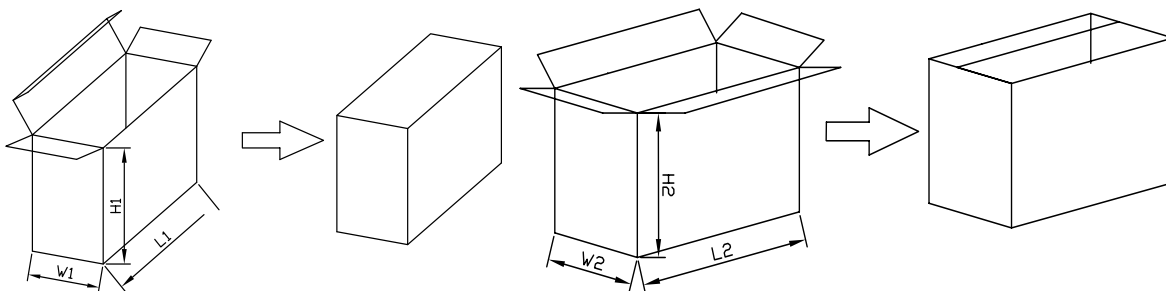
Product model : TSA10 100

PDC information



Packaging Information

1.



Packaging Information

NO	UNIT	Inside Box			Outside Box		
		L1	W1	H1	L2	W2	H2
Size	mm			1		20	0
QTY	PCS	Smallest package, 0PCS			, 00PCS/carton, boxes in total		
Note	Tolerance	20mm,±3mm;	21-100mm,±5mm;	101-500mm,±10mm			